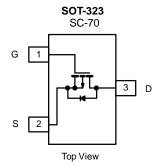


# 2SJ364-VB Datasheet P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	V <sub>GS(th)</sub> (V)	I <sub>D</sub> (mA)			
- 60	4 at V <sub>GS</sub> = - 10 V	- 1 to - 3	- 135			



#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- High-Side Switching
- Low On-Resistance: 4 Ω
- Low Threshold: 2 V (typ.)
- Fast Swtiching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Low input oupdottarioc. 20 pr (typ.)
- Compliant to RoHS Directive 2002/95/EC

#### **APPLICATIONS**

- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- · Battery Operated Systems
- Power Supply Converter Circuits
- · Solid-State Relays

#### **BENEFITS**

- · Ease in Driving Switches
- · Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- · Easily Driven without Buffer

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	- 60	V	
Gate-Source Voltage		$V_{GS}$	± 20	V	
Outline Dute Outline	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 135	mA	
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> = 100 °C		- 105		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 800		
Develop Distriction	T <sub>A</sub> = 25 °C	P <sub>D</sub>	350	mW	
Power Dissipation <sup>a</sup>	T <sub>A</sub> = 100 °C		140		
Maximum Junction-to-Ambient <sup>a</sup>		R <sub>thJA</sub>	350	°C/W	
Operating Junction and Storage Temperature Range		T <sub>J,</sub> T <sub>stg</sub>	- 55 to 150	°C	

#### Notes

- a. Surface mounted on FR4 board.
- b. Pulse width limited by maximum junction temperature.

RoHS COMPLIANT HALOGEN

FREE



			Limits				
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_{D} = -10 \mu\text{A}$	- 60			V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	ľ	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 10	) μΑ	
Cata Bady Laakaga		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$			± 200		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			± 500	nA	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			± 100		
Zero Gate Voltage Drain Current	,	V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V			- 25	1	
	I <sub>DSS</sub>	V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C	/, T <sub>J</sub> = 85 °C		- 250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V, V <sub>DS</sub> = - 4.5 V	- 50			mA	
		V <sub>GS</sub> = - 10 V, V <sub>DS</sub> = - 10 V	- 600				
	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 25 mA		5		Ω	
Drain-Source On-Resistance <sup>a</sup>		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 100 mA		4			
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 100 mA, T <sub>J</sub> =125 °C	T <sub>J</sub> =125 °C		9		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 100 mA	80			mS	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 100 mA, V <sub>GS</sub> = 0 V			- 1.4	٧	
Dynamic	<u> </u>						
Total Gate Charge	Qg			1.7			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = -15 \text{ V}$ $I_{D} \cong -100 \text{ mA}$		0.26		nC	
Gate-Drain Charge	Q <sub>gd</sub>	1D = 100 m/r		0.46			
Input Capacitance	C <sub>iss</sub>			23			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1  MHz		10		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	1 - 1 1/1/12		5			
Switching <sup>b</sup>							
Turn-On Time	t <sub>d(on)</sub>	$V_{DD} = -25 \text{ V}, R_1 = 150 \Omega$		20			
Turn-Off Time	t <sub>d(off)</sub>	$I_D \cong$ - 200 mA, $V_{GEN} = -10 \text{ V}$ , $R_g = 10 \Omega$		35		ns	

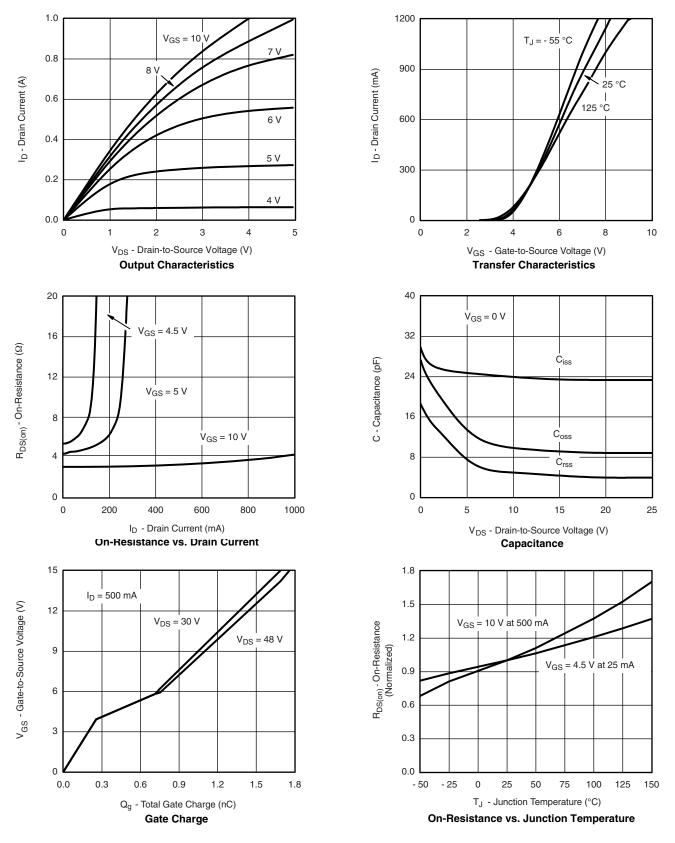
#### Notes:

- a. Pulse test: PW  $\leq$  300  $\mu s$  duty cycle  $\leq$  2 %.
- b. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

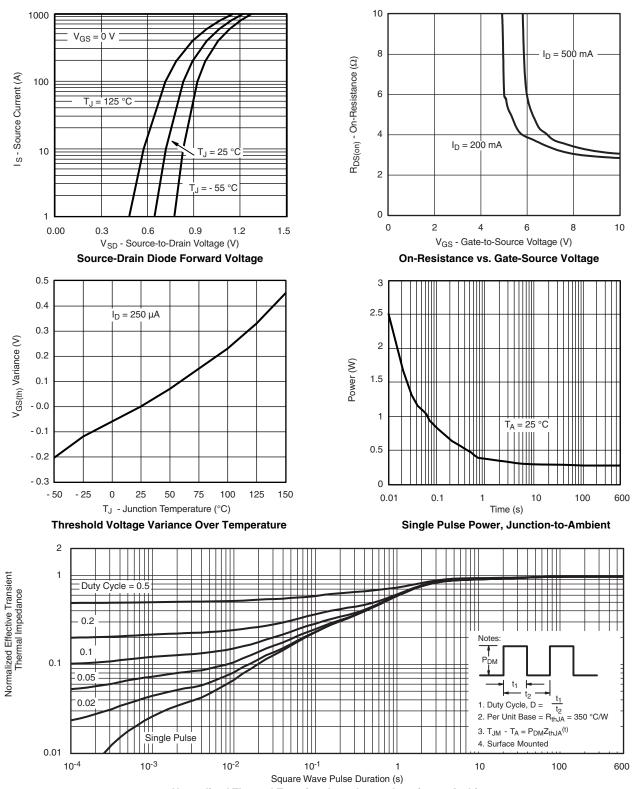


#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





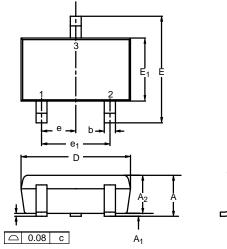
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

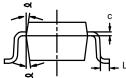


Normalized Thermal Transient Impedance, Junction-to-Ambient



## SC-70: 3-LEADS



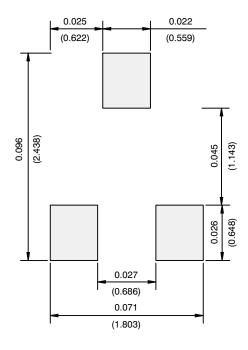


	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.90	_	1.10	0.035	_	0.043
A <sub>1</sub>	-	_	0.10	-	-	0.004
A <sub>2</sub>	0.80	-	1.00	0.031	_	0.039
b	0.25	_	0.40	0.010	_	0.016
С	0.10	_	0.25	0.004	-	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
Ε	1.80	2.10	2.40	0.071	0.083	0.094
E <sub>1</sub>	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65BSC			0.026BSC		
e <sub>1</sub>	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
٦	7°Nom			7°Nom		

ECN: S-03946—Rev. C, 09-Jul-01 DWG: 5549



## **RECOMMENDED MINIMUM PADS FOR SC-70: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)



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